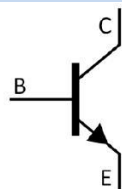


Silicon NPN transistor in a SOT-23 Plastic Package.

Large current capacity and wide ASO.

Small signal general purpose amplifier applications.

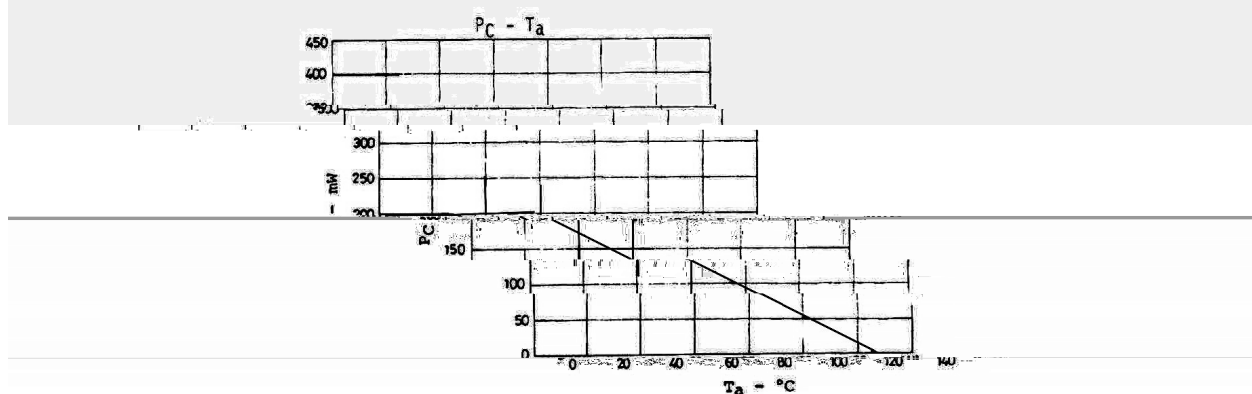
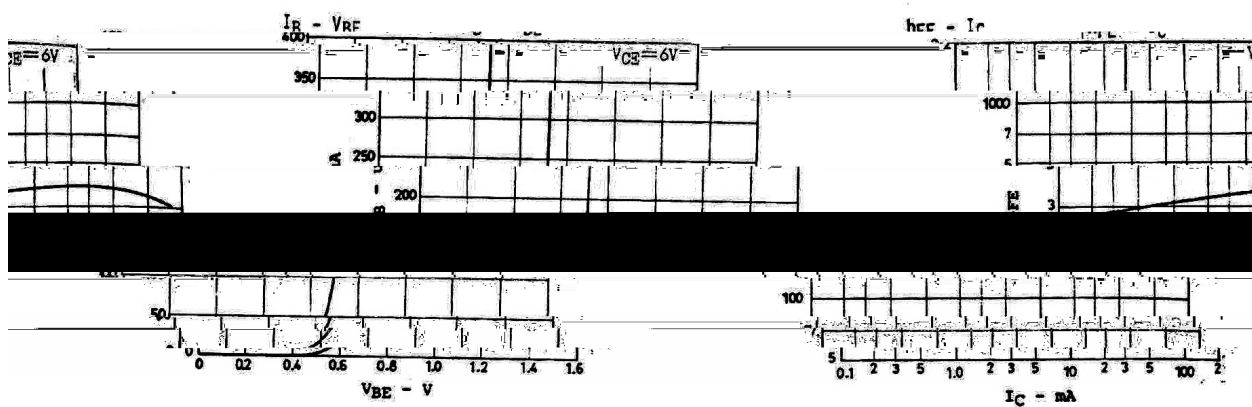


PIN1 Base PIN 2 Emitter PIN 3 Collector

h _{FE} Classifications Symbol	D	E	F	G	H
h _{FE} Range	60 120	100 200	160 320	280 560	480 960
Marking	H53D	H53E	H53F	H53G	H53H

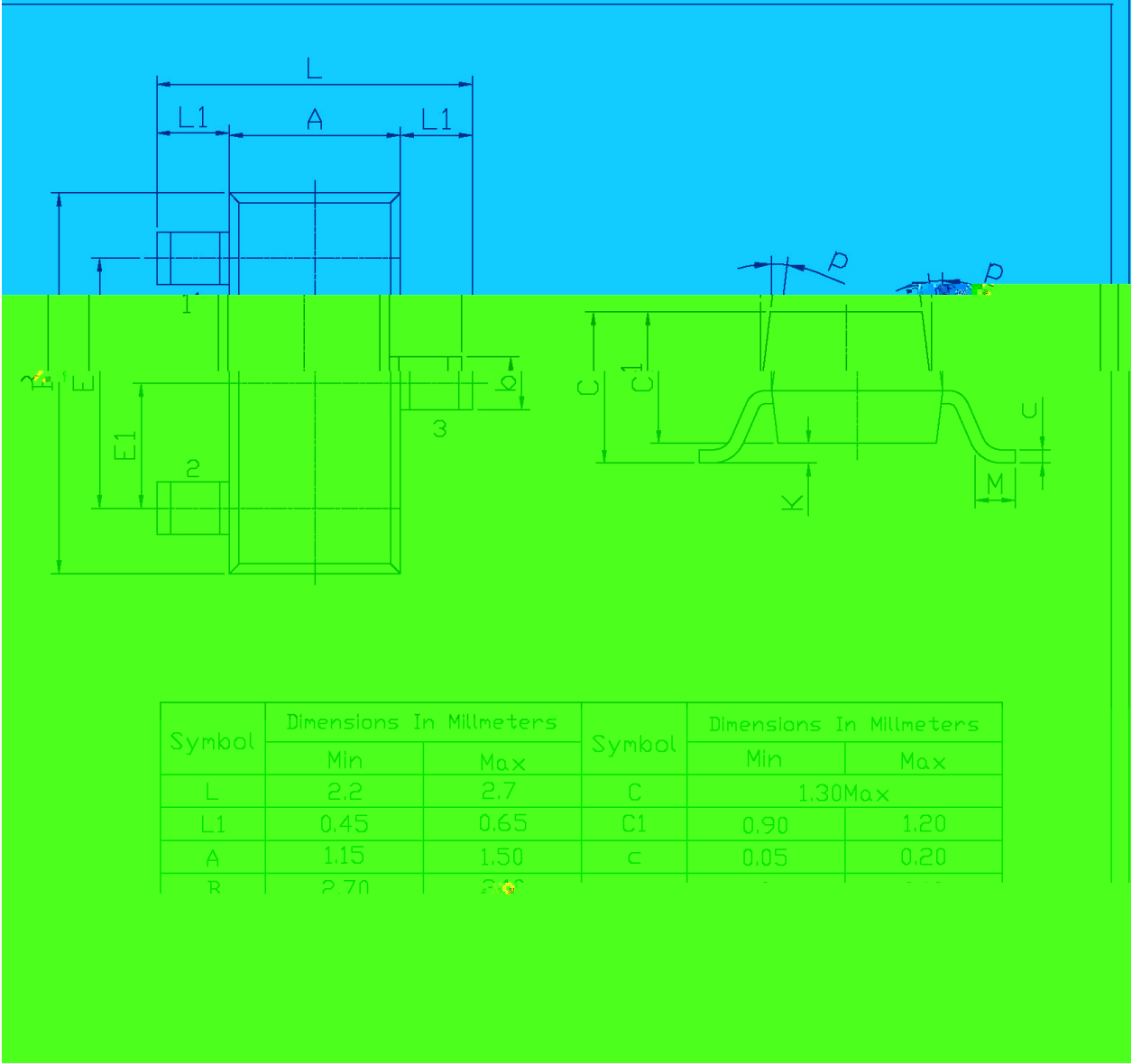
Parameter		Symbol	Rating	Unit
Collector to Base Voltage	2SC536M 2SC536KM	V_{CBO}	40 55	V
Collector to Emitter Voltage	2SC536M 2SC536KM	V_{CEO}	30 50	V
Emitter to Base Voltage		V_{EBO}	5.0	V
Collector Current		I_C	100	mA
Collector Current(pulse)		I_{CP}	300	mA
Collector Power Dissipation		P_C	250	mW
Junction Temperature		T_j	150	
Storage Temperature Range		T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=35V$ $I_E=0$			1.0	μA
Emitter Base Cut-Off Current	I_{EBO}	$V_{EB}=4.0V$ $I_C=0$			1.0	μA
DC Current Gain	h_{FE}	$V_{CE}=6.0V$ $I_C=1.0mA$	60		960	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=50mA$ $I_B=5.0mA$			0.5	V
Transition Frequency	f_T	$V_{CE}=6.0V$ $I_C=1.0mA$		100		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=6.0V$ $f=1.0MHz$ $I_E=0$		3.5		pF
Collector- Base Time Constant	$C_{C-rbb'}$	$V_{CB}=6.0V$ $f=31.9MHz$ $I_C=1.0mA$		250		pS

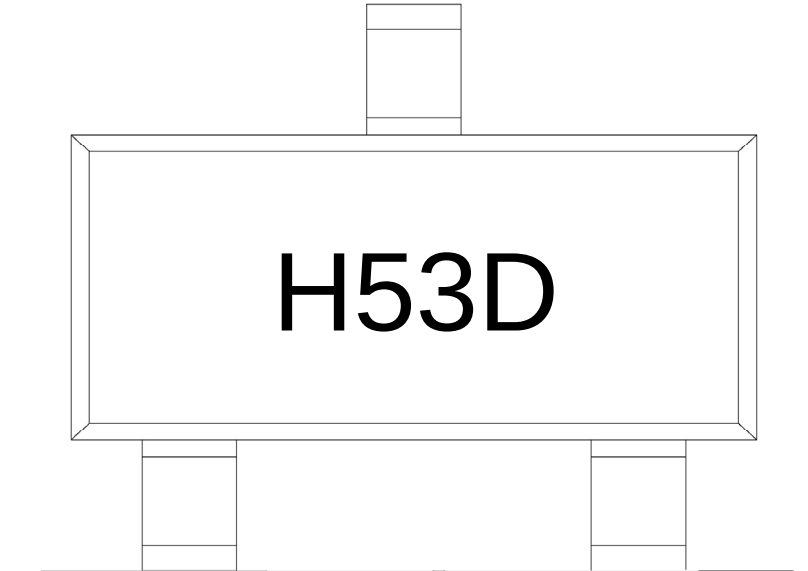


SOT-23

单位: mm



Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
L	2.2	2.7	C	1.30Max	
L1	0.45	0.65	C1	0.90	1.20
A	1.15	1.50	c	0.05	0.20
R	2.70	2.65			



h_{FE}

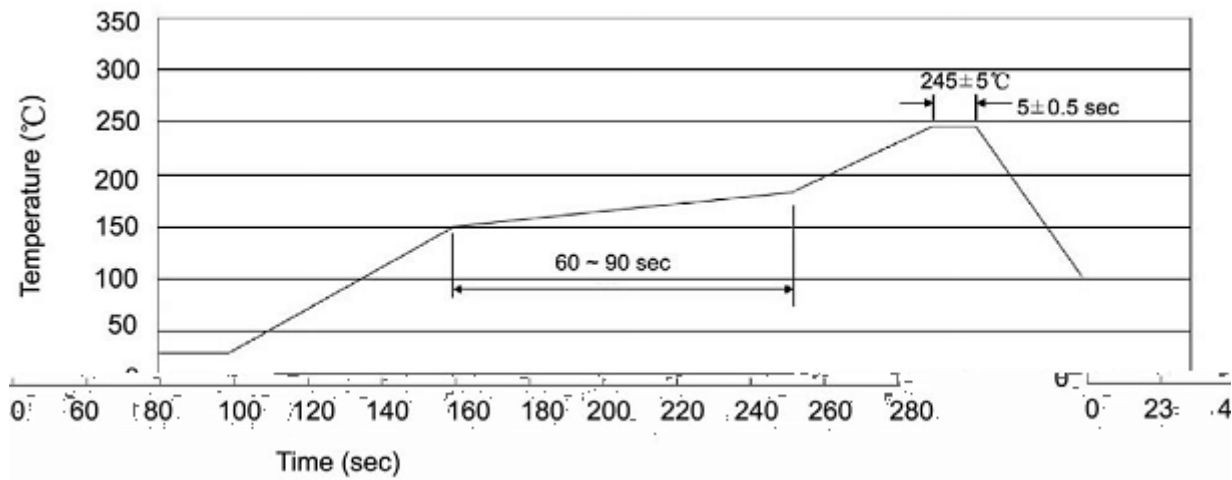
Note:

Company Code

Product Type Code

h_{FE} Classifications Symbol Code

Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- 1

25 150

60 90sec;
- 2

245 5

5 0.5sec;
- 3

2 10

/sec.
- 1.Preheating:25~150

, Time:60~90sec.
- 2.Peak Temp.:245 5

, Duration:5 0.5sec.
3. Cooling Speed: 2~10

/sec.

260 5

10 1 sec.

Temp.:260 5

Time:10 1 sec

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 卷盘	卷盘 盒	只 盒	盒 箱	只 箱		盒	箱